



QUAD DIFFERENTIAL PECL RECEIVERS

FEATURES

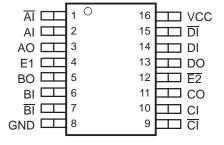
- Functional Replacement for the Agere BRF1A
- Pin Equivalent to General Trade 26LS32
- High Input Impedance Approximately 8 kΩ
- <2.6-ns Maximum Propagation Delay
- TB5R3 Provides 50-mV Hysteresis (Typical)
- -1.1-V to 7.1-V Common-Mode Input Voltage Range
- Single 5-V ±10% Supply
- ESD Protection HBM > 3 kV and CDM > 2 kV
- Operating Temperature Range: -40°C to 85°C
- Available in Gull-Wing SOIC (JEDEC MS-013, DW) and SOIC (D) Package

APPLICATIONS

 Digital Data or Clock Transmission Over Balanced Lines

PIN ASSIGNMENTS

SOIC PACKAGE (TOP VIEW)



DESCRIPTION

These quad differential receivers accept digital data over balanced transmission lines. They translate differential input logic levels to TTL output logic levels.

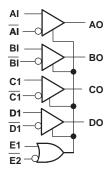
The TB5R3 is a pin- and function-compatible replacement for the Agere systems BRF1A; it includes 3-kV HBM and 2-kV CDM ESD protection.

The power-down loading characteristics of the receiver input circuit are approximately 8 $k\Omega$ relative to the power supplies; hence they do not load the transmission line when the circuit is powered down.

The packaging for this differential line receiver is a 16-pin gull wing SOIC (DW) or a 16 pin SOIC (D).

The enable inputs of this device include internal pull-up resistors of approximately 40 k Ω that are connected to V_{CC} to ensure a logical high level input if the inputs are open circuited.

FUNCTIONAL BLOCK DIAGRAM



Enable Truth Table

E1	E2	OUTPUT CONDITION
0	0	Active
1	0	Active
0	1	Disabled
1	1	Active



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

PART NUMBER (1)	MBER ⁽¹⁾ PART MARKING PACKAGE ⁽²⁾		LEAD FINISH	STATUS
TB5R3DW	TB5R3	Gull-Wing SOIC	NiPdAu	Production
TB5R3D	TB5R3	SOIC	NiPdAu	Production

⁽¹⁾ Add the R suffix for tape and reel carrier (i.e., TB5R3DR)

POWER DISSIPATION RATINGS

PACKAGE	GE CIRCUIT BOARD POWER RATING $T_A \le 25^{\circ}C$		IUNCTION-TO-AMBIENT		POWER RATING T _A = 85°C
DW	Low-K ⁽²⁾	831 mW	120.3°C/W	8.3 mW/°C	332 mW
DVV	High-K ⁽³⁾	1240 mW	80.8°C/W	12.4 mW/°C	494 mW
	Low-K ⁽²⁾	763 mW	131.1°C/W	7.6 mW/°C	305 mW
D	High-K ⁽³⁾	1190 mW	84.1°C/W	11.9 mW/°C	475 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted with no air flow.

THERMAL CHARACTERISTICS

	PARAMETER	PACKAGE	VALUE	UNIT
0	lunction to Donal Thomas Decistors	DW	53.7	0000
θ_{JB}	Junction-to-Board Thermal Resistance	D	47.5	°C/W
$\theta_{\sf JC}$	hunding to Cons Thomas Decistors	DW	47.1	0000
	Junction-to-Case Thermal Resistance	D	44.2	°C/W

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

			UNIT
Supply voltage, V _{CC}			0 V to 6 V
Magnitude of d	Magnitude of differential bus (input) voltage, $ V_{AI} - V_{AI} $, $ V_{BI} - V_{BI} $, $ V_{CI} - V_{CI} $, $ V_{DI} - V_{DI} $		
TCD.	Human Body Model (2)	All pins	±3.5 kV
ESD	Charged-Device Model (3)	All pins	±2 kV
Continuous po	Continuous power dissipation		See Dissipation Rating Table
Storage temperature, T _{stg}		-65°C to 150°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Product Folder Link(s): TB5R3

⁽²⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

²⁾ In accordance with the low-K thermal metric definitions of EIA/JESD51-3.

⁽³⁾ In accordance with the high-K thermal metric definitions of EIA/JESD51-7.

⁽²⁾ Tested in accordance with JEDEC Standard 22, Test Method A114-A.

⁽³⁾ Tested in accordance with JEDEC Standard 22, Test Method C101.



RECOMMENDED OPERATING CONDITIONS

	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}	4.5	5	5.5	V
Bus pin input voltage, V_{AI} , V_{AI} , $V_{BI}V_{BI}$, V_{CI} , or V_{CI} , V_{DI} , $V_{\overline{DI}}$	-1.2 ⁽¹⁾		7.2	V
Magnitude of differential input voltage, $ V_{AI} - V_{\overline{AI}} $, $ V_{BI} - V_{\overline{BI}} $, $ V_{CI} - V_{\overline{CI}} $, $ V_{DI} - V_{\overline{DI}} $	0.1		6	V
Low-level enable input voltage $^{(2)}$, V_{IL} ($V_{CC} = 5.5 \text{ V}$)			0.8	V
High-level enable input voltage ⁽²⁾ , V _{IH} (V _{CC} = 5.5 V)	2			V
Operating free-air temperature, T _A	-40		85	°C

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet, unless otherwise noted.

DEVICE ELECTRICAL CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Supply ourront(1)	Outputs disabled			50	mA
IC	Supply current ⁽¹⁾	Outputs enabled			48	mA

⁽¹⁾ Current is dc power draw as measured through GND pin and does not include power delivered to load.

RECEIVER ELECTRICAL CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
V _{OL}	Output low voltage	$V_{CC} = 4.5 \text{ V},$	$I_{OL} = 8 \text{ mA}$			0.4	V
V _{OH}	Output high voltage	$V_{CC} = 4.5 \text{ V},$	I _{OH} = -400 μA	2.4			V
V _{IK}	Enable input clamp voltage	$V_{CC} = 4.5 \text{ V},$	I _I = -5 mA			-1 ⁽¹⁾	V
V _{TH+}	Positive-going differential input threshold voltage ⁽²⁾ , $(V_{xl} - V_{\overline{xt}})$	x = A, B, C, or	D			100	mV
V _{TH-}	Negative-going differential input threshold voltage $^{(2)}$, $(V_{xl}$ - $V_{\overline{xl}})$	x = A, B, C, or	D			100 ⁽¹⁾	mV
V_{HYST}	Differential input threshold voltage hysteresis, $(V_{TH+} - V_{TH-})$				50		mV
I _{OZL}	Output off state surrent (High 7)	\/ F.F.\/	V _O = 0.4 V			-20 ⁽¹⁾	μA
I _{OZH}	Output off-state current, (High-Z)	$V_{CC} = 5.5 \text{ V}$	V _O = 2.4 V			20	μΑ
I _{OS}	Output short circuit current	V _{CC} = 5.5 V				400 ⁽¹⁾	mA
I _{IL}	Enable input low current	V _{CC} = 5.5 V,	$V_{IN} = 0.4 V$			400 ⁽¹⁾	μA
	Enable input high current	\/ F.F.\/	V _{IN} = 2.7 V			20	μΑ
I _{IH}	Enable input reverse current	$V_{CC} = 5.5 \text{ V}$	V _{IN} = 5.5 V			100	μΑ
I _{IL}	Differential input low current	$V_{CC} = 5.5V$,	V _{IN} = -1.2 V			-2 ⁽¹⁾	mA
I _{IH}	Differential input high current	V _{CC} = 5.5V,	V _{IN} = 7.2 V			1	mA
D	Small aignal output registance	Output High			50		0
R _O	Small-signal output resistance	Output Low			25		Ω

⁽¹⁾ This parameter is listed using a magnitude and polarity/direction convention, rather than an algebraic convention, to match the original Agere data sheet.

Product Folder Link(s): TB5R3

⁽²⁾ The input levels and difference voltage provide no noise immunity and should be tested only in a static, noise-free environment.

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SWITCHING CHARACTERISTICS

over operating free-air temperature range unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output	$C_L = 0 pF^{(1)},$		1.64	<2.6	20
t _{PHL}	Propagation delay time, high-to-low-level output	See Figure 2 and Figure 4		1.57	<2.6	ns
t _{PLH}	Propagation delay time, low-to-high-level output	C FORE See Figure 2 and Figure 4(2)		2.2	3.5	20
t _{PHL}	Propagation delay time, high-to-low-level output	$C_L = 50 \text{ pF}$, See Figure 2 and Figure 4 ⁽²⁾		2.1	3.5	ns
t _{PHZ}	Output disable time, high-level-to-high-impedance output (3)	C F DE Coo Figure 2 and Figure 5		7.7	12	ns
t _{PLZ}	Output disable time, low-level-to-high-impedance output (3)	C _L = 5 pF, See Figure 3 and Figure 5		5.2	12	ns
	Dules width distantian It 4	C _L = 10 pF, See Figure 2 and Figure 4			0.7	ns
t _{skew1}	Pulse-width distortion, t _{PHL} - t _{PLH}	C _L = 150 pF, See Figure 2 and Figure 4			4	ns
Δt_{skew1p}	Part-to-part output waveform skew	$C_L = 10 \text{ pF}, T_A = 75^{\circ}\text{C}, \text{ See Figure 2 and }$ Figure 4		0.8	1.4	ns
-p	·	C _L = 10 pF, See Figure 2 and Figure 4			1.5	ns
Δt_{skew}	Same part output waveform skew	C _L = 10 pF, See Figure 2 and Figure 4			0.3	ns
t _{PZH}	Output enable time, high-impedance-to-high-level output (3)	0 40 75 0 75 77 77 0 74 5 77 74		6.9	12	ns
t _{PZL}	Output enable time, high-impedance-to-low-level output (3)	C _L = 10 pF, See Figure 3 and Figure 4		6.3	12	ns
t _{TLH}	Rise time (20%-80%)	C 10 pF Coo Figure 2 and Figure 4			1	ns
t _{THL}	Fall time (80%-20%)	C _L = 10 pF, See Figure 2 and Figure 4			1	ns

The propagation delay values with a 0 pF load are based on design and simulation.

See Table 1.

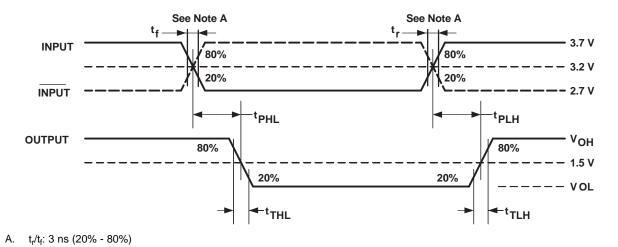
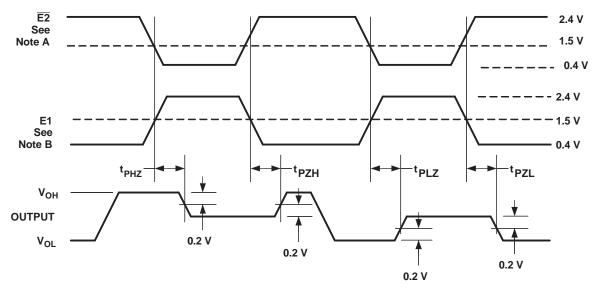


Figure 1. Receiver Propagation Delay Times

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⁽²⁾ (3) t_r/t_f: 3 ns (20% - 80%)

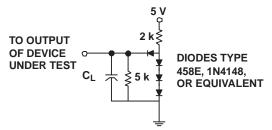




- A. $\overline{E2} = 1$ while E1 changes states.
- B. E1 = 0 while $\overline{E2}$ changes states.

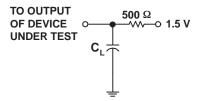
Figure 2. Receiver Enable and Disable Timing

Parametric values specified under the Electrical Characteristics and Timing Characteristics sections for the data transmission driver devices are measured with the following output load circuits.



 $\mathbf{C}_{\mathbf{L}}$ includes test-fixture and probe capacitance.

Figure 3. Receiver Propagation Delay Time and Enable Time (t_{PZH}, t_{PZL}) Test Circuit



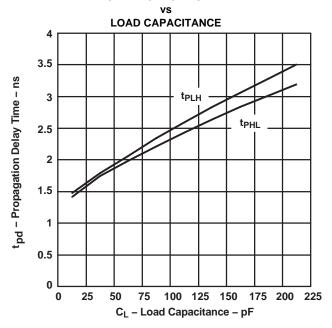
C₁ includes test-fixture and probe capacitance.

Figure 4. Receiver Disable Time ($t_{PHZ},\,t_{PLZ}$) Test Circuit



TYPICAL CHARACTERISTICS

TYPICAL PROPAGATION DELAY



NOTE: This graph is included as an aid to the system designers. Total circuit delay varies with load capacitance. The total delay is the sum of the delay due to external capacitance and the intrinsic delay of the device. Intrinsic delay is listed in the table above as the 0 pF load condition. The incremental increase in delay between the 0 pF load condition and the actual total load capacitance represents the extrinsic, or external delay contributed by the load.

Figure 5.

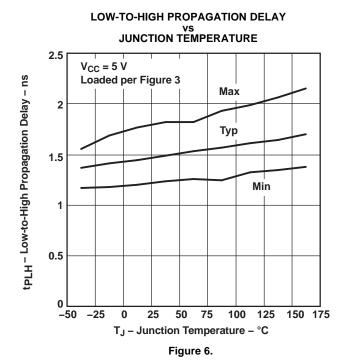
HIGH-TO-LOW PROPAGATION DELAY



TYPICAL CHARACTERISTICS (continued)

-50

-25



JUNCTION TEMPERATURE 2.5 V_{CC} = 5 V, Loaded per Figure 3 Typ Typ Min 0.5

75

100

125

150

50

T_J - Junction Temperature - °C

Figure 7.

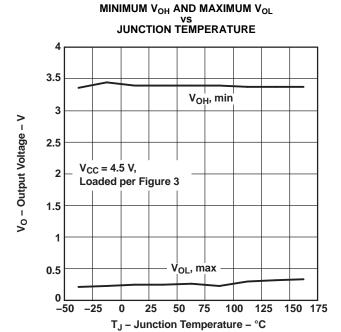
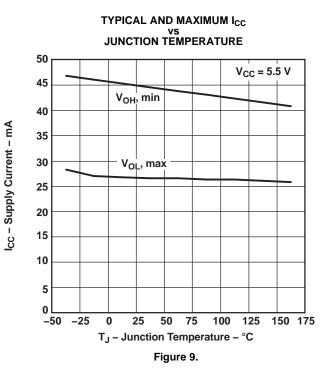


Figure 8.





APPLICATION INFORMATION

Power Dissipation

The power dissipation rating, often listed as the package dissipation rating, is a function of the ambient temperature, T_A , and the airflow around the device. This rating correlates with the device's maximum junction temperature, sometimes listed in the absolute maximum ratings tables. The maximum junction temperature accounts for the processes and materials used to fabricate and package the device, in addition to the desired life expectancy.

There are two common approaches to estimating the internal die junction temperature, T_J . In both of these methods, the device internal power dissipation P_D needs to be calculated This is done by totaling the supply power(s) to arrive at the system power dissipation:

$$\sum (V_{Sn} \times I_{Sn}) \tag{1}$$

and then subtracting the total power dissipation of the external load(s):

$$\sum (V_{Ln} \times I_{Ln}) \tag{2}$$

The first T_J calculation uses the power dissipation and ambient temperature, along with one parameter: $\theta_{JA},\;$ the junction-to-ambient thermal resistance, in degrees Celsius per watt.

The product of P_D and θ_{JA} is the junction temperature rise above the ambient temperature. Therefore:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA}) \tag{3}$$

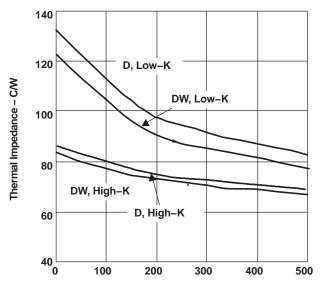


Figure 10. Thermal Impedance vs Air Flow

Note that θ_{JA} is highly dependent on the PCB on

which the device is mounted and on the airflow over the device and PCB. JEDEC/EIA has defined standardized test conditions for measuring $\theta_{JA}.$ Two commonly used conditions are the low-K and the high-K boards, covered by EIA/JESD51-3 and EIA/JESD51-7 respectively. Figure 10 shows the low-K and high-K values of θ_{JA} versus air flow for this device and its package options.

The standardized θ_{JA} values may not accurately represent the conditions under which the device is used. This can be due to adjacent devices acting as heat sources or heat sinks, to nonuniform airflow, or to the system PCB having significantly different thermal characteristics than the standardized test PCBs. The second method of system thermal analysis is more accurate. This calculation uses the power dissipation and ambient temperature, along with two device and two system-level parameters:

- θ_{JC}, the junction-to-case thermal resistance, in degrees Celsius per watt
- θ_{JB}, the junction-to-board thermal resistance, in degrees Celsius per watt
- θ_{CA} , the case-to-ambient thermal resistance, in degrees Celsius per watt
- θ_{BA}, the board-to-ambient thermal resistance, in degrees Celsius per watt.

In this analysis, there are two parallel paths, one through the case (package) to the ambient, and another through the device to the PCB to the ambient. The system-level junction-to-ambient thermal impedance, $\theta_{\text{JA(S)}}$, is the equivalent parallel impedance of the two parallel paths:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA(S)})$$
(4)

where

$$\theta_{\text{JA(S)}} = \frac{\left[\left(\theta_{\text{JC}} + \theta_{\text{CA}} \right) \times \left(\theta_{\text{JB}} + \theta_{\text{BA}} \right) \right]}{\left(\theta_{\text{JC}} + \theta_{\text{CA}} + \theta_{\text{JB}} + \theta_{\text{BA}} \right)} \tag{5}$$

The device parameters θ_{JC} and θ_{JB} account for the internal structure of the device. The system-level parameters θ_{CA} and θ_{BA} take into account details of the PCB construction, adjacent electrical and mechanical components, and the environmental conditions including airflow. Finite element (FE), finite difference (FD), or computational fluid dynamics (CFD) programs can determine θ_{CA} and $\theta_{BA}.$ Details on using these programs are beyond the scope of this data sheet, but are available from the software manufacturers.

www.ti.com 11-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
TB5R3DW	Last Time Buy	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TB5R3
TB5R3DW.B	Last Time Buy	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TB5R3

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

www.ti.com 23-May-2025

TUBE



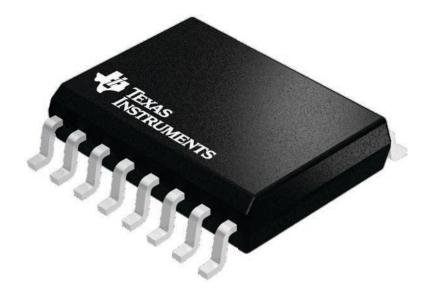
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TB5R3DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
TB5R3DW.B	DW	SOIC	16	40	506.98	12.7	4826	6.6

7.5 x 10.3, 1.27 mm pitch

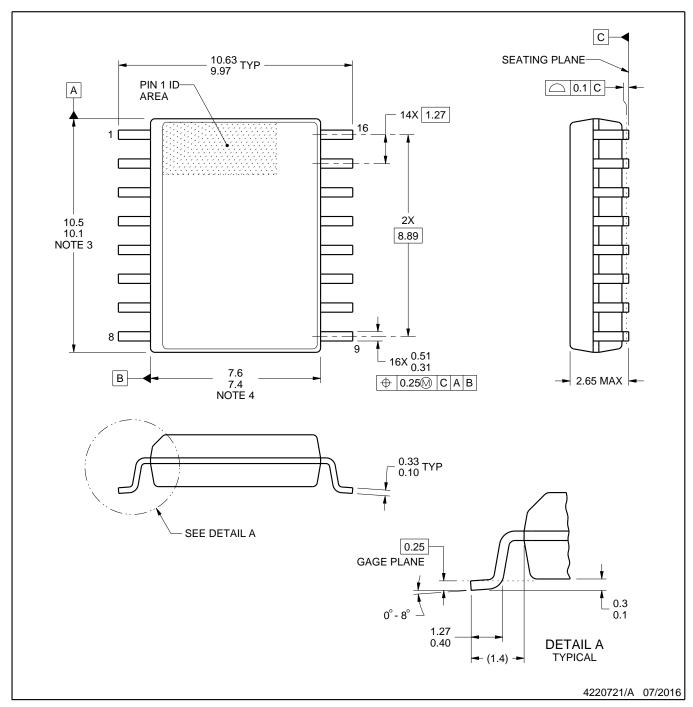
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



NOTES:

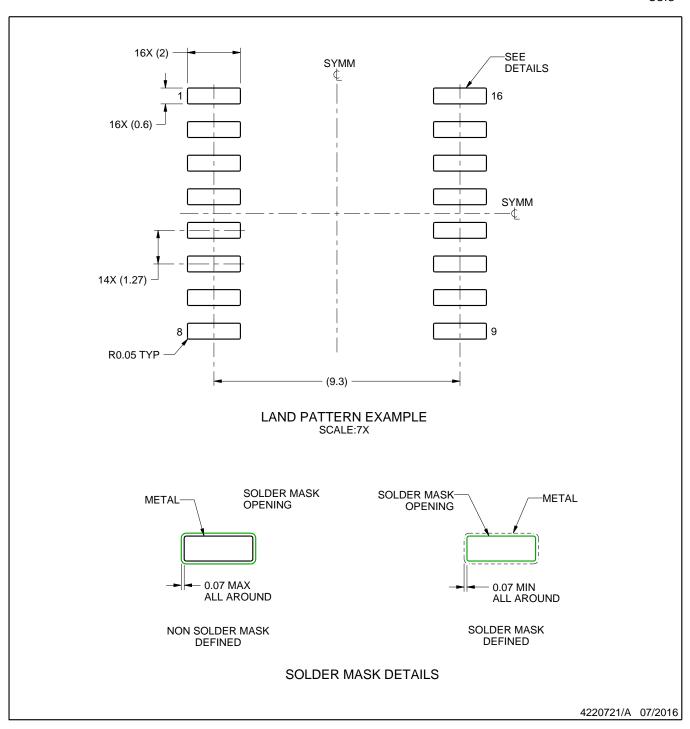
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



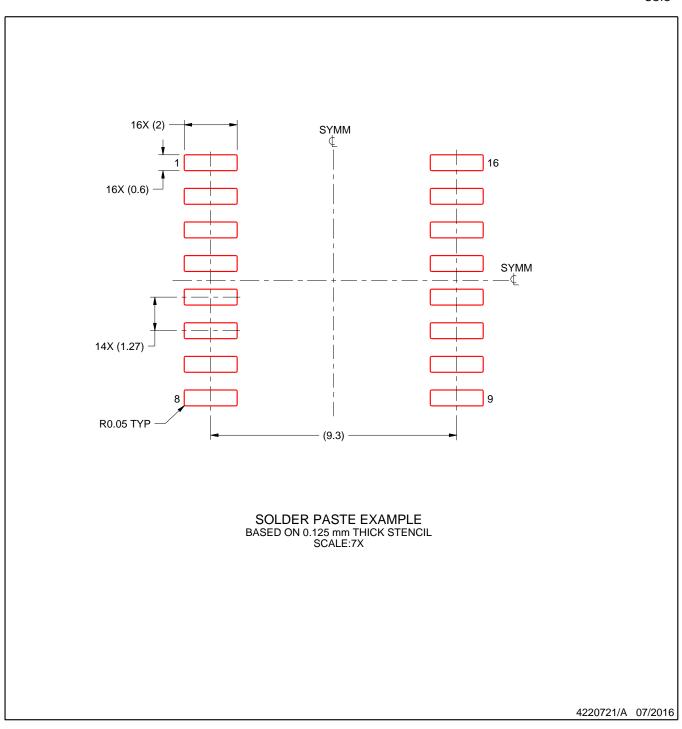
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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